



**FM200TU-3A**

**HIGH POWER SWITCHING USE  
INSULATED PACKAGE**

**ABSOLUTE MAXIMUM RATINGS (Tch = 25°C unless otherwise specified.)**

Symbol	Item	Conditions	Ratings	Unit
V <sub>DSS</sub>	Drain-source voltage	G-S Short	150	V
V <sub>GSS</sub>	Gate-source voltage	D-S Short	±20	V
I <sub>D</sub>	Drain current	T <sub>C</sub> ' = 122°C* <sup>3</sup>	100	A
I <sub>DM</sub>		Pulse* <sup>2</sup>	200	A
I <sub>DA</sub>	Avalanche current	L = 10μH Pulse* <sup>2</sup>	100	A
I <sub>S</sub> * <sup>1</sup>	Source current		100	A
I <sub>SM</sub> * <sup>1</sup>		Pulse* <sup>2</sup>	200	A
P <sub>D</sub> * <sup>4</sup>	Maximum power dissipation	T <sub>C</sub> = 25°C	410	W
P <sub>D</sub> * <sup>4</sup>		T <sub>C</sub> ' = 25°C* <sup>3</sup>	560	W
T <sub>ch</sub>	Channel temperature		-40 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-40 ~ +125	°C
V <sub>iso</sub>	Isolation voltage	Main terminal to base plate, AC 1 min.	2500	V
—	Mounting torque	Main Terminal M6	3.5 ~ 4.5	N • m
		Mounting M6	3.5 ~ 4.5	N • m
—	Weight	Typical value	600	g

**ELECTRICAL CHARACTERISTICS (Tch = 25°C unless otherwise specified.)**

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I <sub>DSS</sub>	Drain cutoff current	V <sub>DS</sub> = V <sub>DSS</sub> , V <sub>GS</sub> = 0V	—	—	1	mA	
V <sub>GS(th)</sub>	Gate-source threshold voltage	I <sub>D</sub> = 10mA, V <sub>DS</sub> = 10V	4.7	6	7.3	V	
I <sub>GSS</sub>	Gate leakage current	V <sub>GS</sub> = V <sub>GSS</sub> , V <sub>DS</sub> = 0V	—	—	1.5	μA	
r <sub>DS(ON)</sub>	Static drain-source (chip) On-state resistance	I <sub>D</sub> = 100A V <sub>GS</sub> = 15V	T <sub>ch</sub> = 25°C	—	4.8	6.6	mΩ
r <sub>DS(ON)</sub>			T <sub>ch</sub> = 125°C	—	9.1	—	
V <sub>DS(ON)</sub>	Static drain-source (chip) On-state voltage	I <sub>D</sub> = 100A V <sub>GS</sub> = 15V	T <sub>ch</sub> = 25°C	—	0.8	1.66	V
V <sub>DS(ON)</sub>			T <sub>ch</sub> = 125°C	—	0.9	—	
R <sub>(lead)</sub>	Lead resistance	I <sub>D</sub> = 100A terminal-chip	T <sub>ch</sub> = 25°C	—	1.2	—	mΩ
R <sub>(lead)</sub>			T <sub>ch</sub> = 125°C	—	1.68	—	
C <sub>iss</sub>	Input capacitance	V <sub>DS</sub> = 10V V <sub>GS</sub> = 0V	—	—	50	nF	
C <sub>oss</sub>	Output capacitance		—	—	7		
C <sub>rss</sub>	Reverse transfer capacitance		—	—	4		
Q <sub>G</sub>	Total gate charge	V <sub>DD</sub> = 80V, I <sub>D</sub> = 100A, V <sub>GS</sub> = 15V	—	820	—	nC	
t <sub>d(on)</sub>	Turn-on delay time	V <sub>DD</sub> = 80V, I <sub>D</sub> = 100A, V <sub>GS1</sub> = V <sub>GS2</sub> = 15V R <sub>G</sub> = 13Ω, Inductive load switching operation I <sub>S</sub> = 100A	—	—	400	ns	
t <sub>r</sub>	Turn-on rise time		—	—	250		
t <sub>d(off)</sub>	Turn-off delay time		—	—	450		
t <sub>f</sub>	Turn-off fall time		—	—	200		
t <sub>rr</sub> * <sup>1</sup>	Reverse recovery time		—	—	200		
Q <sub>rr</sub> * <sup>1</sup>	Reverse recovery charge		—	6.5	—		μC
V <sub>SD</sub> * <sup>1</sup>	Source-drain voltage	I <sub>S</sub> = 100A, V <sub>GS</sub> = 0V	—	—	1.3	V	
R <sub>th(ch-c)</sub>	Thermal resistance	MOSFET part (1/6 module)* <sup>7</sup>	—	—	0.30	°C/W	
R <sub>th(ch-c')</sub>		MOSFET part (1/6 module)* <sup>3</sup>	—	—	0.22		
R <sub>th(c-f)</sub>	Contact thermal resistance	Case to fin, Thermal grease Applied* <sup>8</sup> (1/6 module)	—	0.1	—		
R <sub>th(c'-f)</sub>		Case to fin, Thermal grease Applied* <sup>3, 8</sup> (1/6 module)	—	0.09	—		

**THERMISTOR PART**

Symbol	Parameter	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R <sub>TH</sub> * <sup>6</sup>	Resistance	T <sub>TH</sub> = 25°C* <sup>5</sup>	—	100	—	kΩ
B* <sup>6</sup>	B Constant	Resistance at T <sub>TH</sub> = 25°C, 50°C* <sup>5</sup>	—	4000	—	K

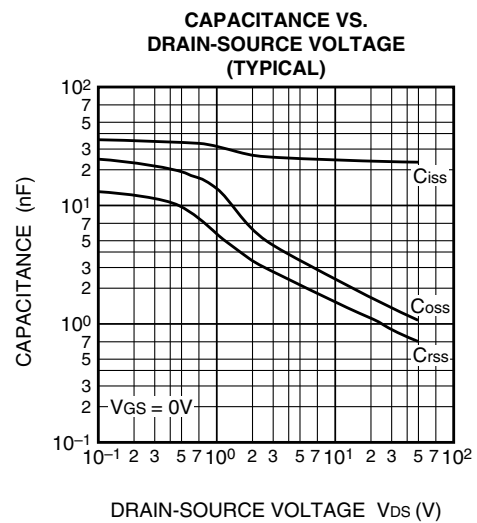
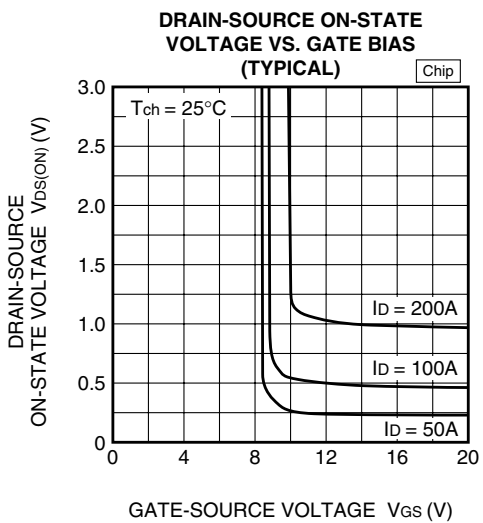
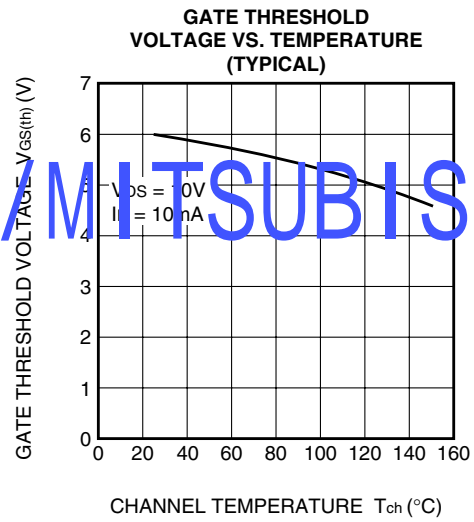
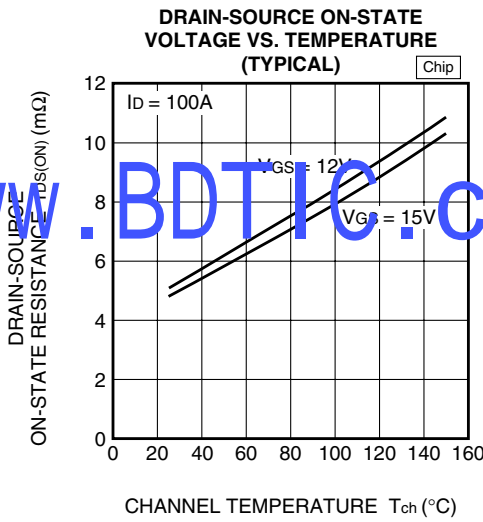
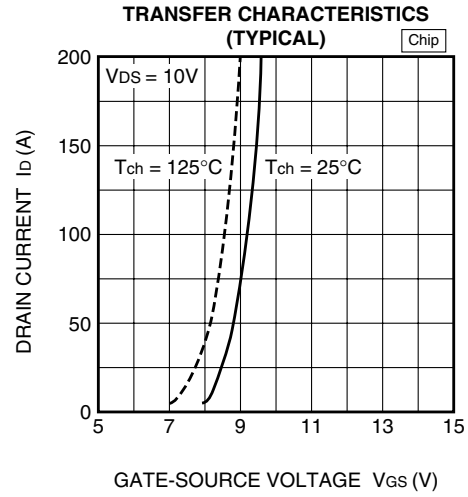
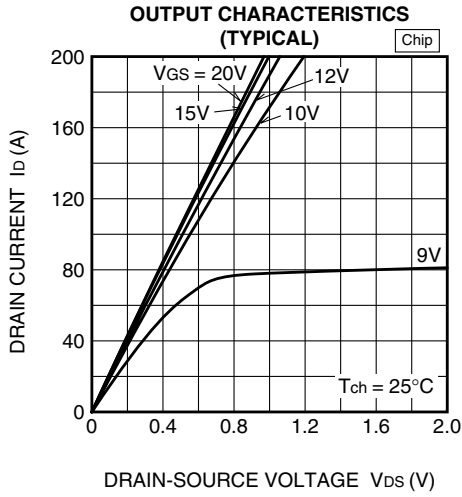
\*1: It is characteristics of the anti-parallel, source to drain free-wheel diode (FWDi).  
 \*2: Pulse width and repetition rate should be such that the device channel temperature (T<sub>ch</sub>) does not exceed T<sub>ch</sub> max rating.  
 \*3: T<sub>C</sub>' measured point is just under the chips. If use this value, R<sub>th(f-a)</sub> should be measured just under the chips.  
 \*4: Pulse width and repetition rate should be such as to cause negligible temperature rise.  
 \*5: T<sub>TH</sub> is thermistor temperature.  
 \*6: B = (lnR<sub>1</sub>-lnR<sub>2</sub>)/(1/T<sub>1</sub>-1/T<sub>2</sub>) R<sub>1</sub>: Resistance at T<sub>1</sub>(K), R<sub>2</sub>: Resistance at T<sub>2</sub>(K)  
 \*7: T<sub>C</sub> measured point is shown in page OUTLINE DRAWING.  
 \*8: Typical value is measured by using Shin-Etsu Chemical Co., Ltd "G-746".



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HIGH POWER SWITCHING USE  
INSULATED PACKAGE

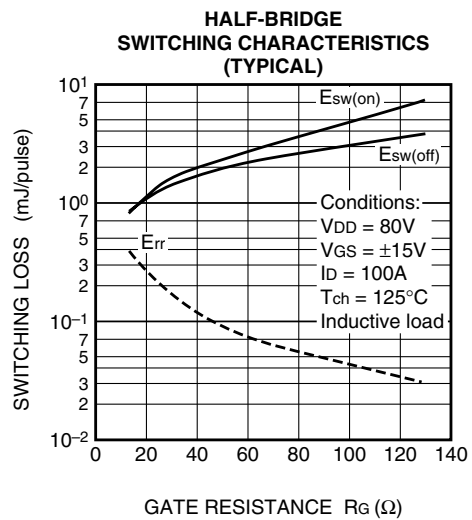
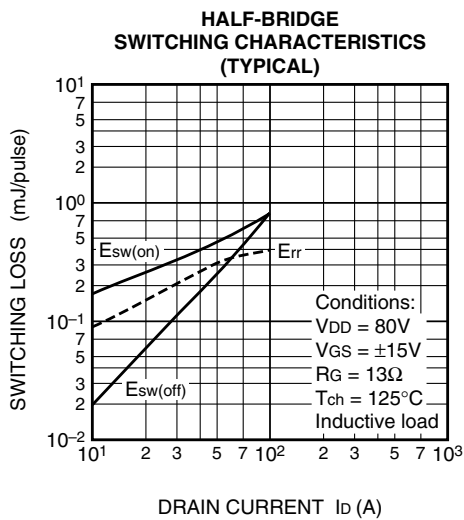
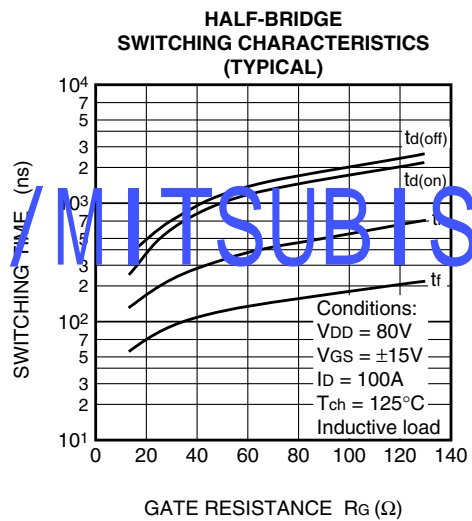
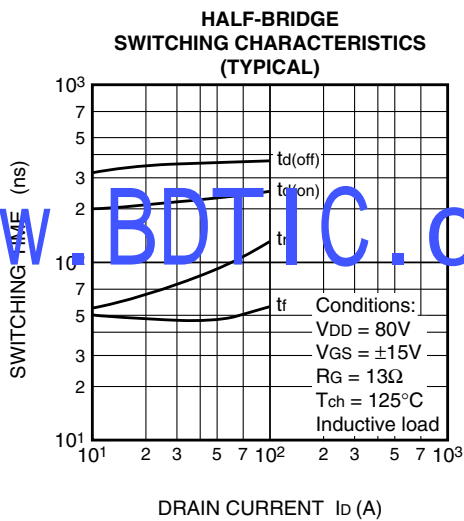
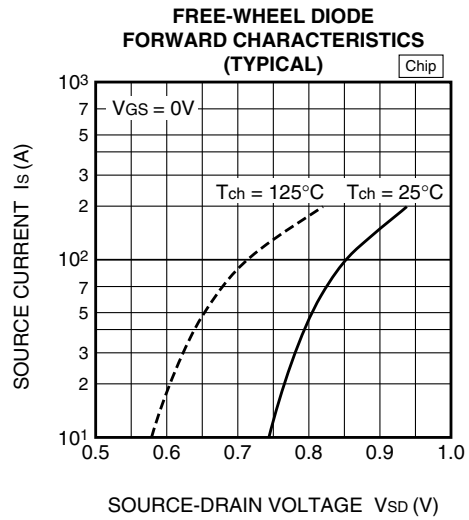
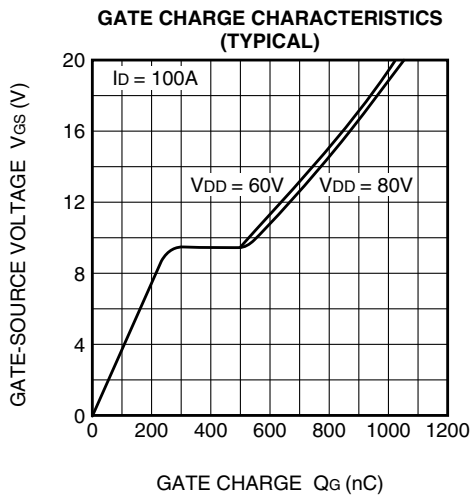
## PERFORMANCE CURVES



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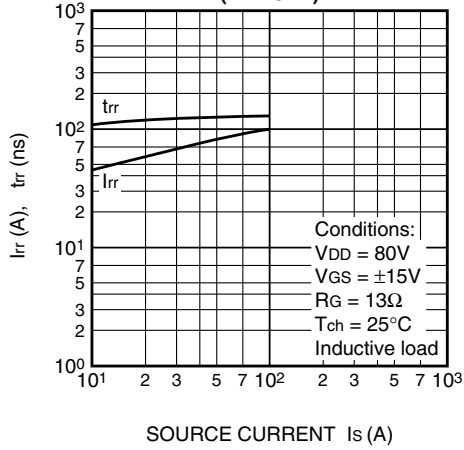


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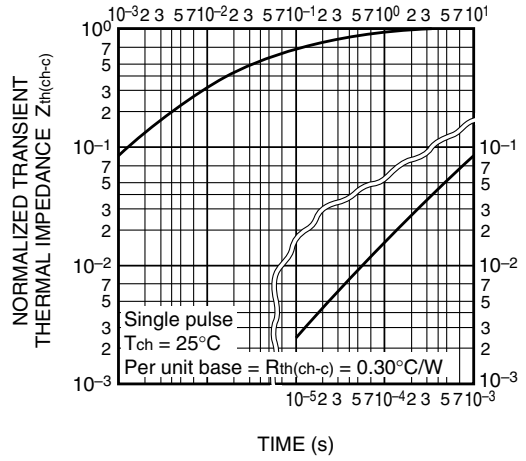
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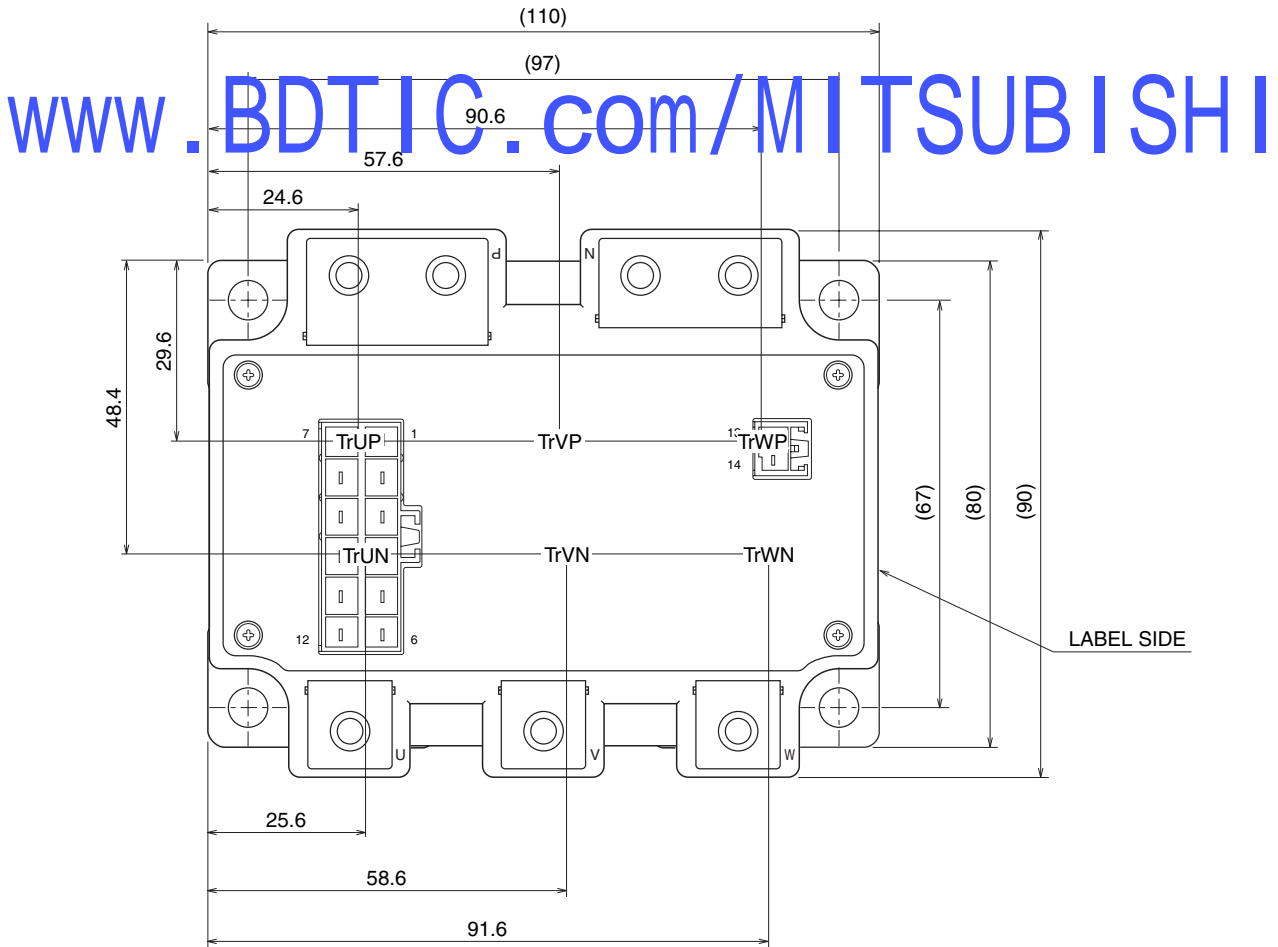
REVERSE RECOVERY CHARACTERISTICS  
OF FREE-WHEEL DIODE  
(TYPICAL)



TRANSIENT THERMAL  
IMPEDANCE CHARACTERISTICS



CHIP LAYOUT



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